

A cross-sectional view of a semiconductor device. A central block (2) is surrounded by a material (4) containing a pattern of '+' signs. A horizontal layer (7') is positioned above the central block. A layer (3) is on top of the central block. A layer (5') is on the bottom surface of the central block. A layer (6) is on the bottom surface of the central block. A layer (6a) is on the bottom surface of the central block. A layer (8) is on the bottom surface of the central block. A layer (11') is on the top surface of the central block. A layer (12') is on the top surface of the central block. A layer (1') is on the top surface of the central block. A layer (7) is on the top surface of the central block. A layer (5c) is on the bottom surface of the central block. A layer (5c') is on the bottom surface of the central block. A layer (5b) is on the bottom surface of the central block. A layer (5b') is on the bottom surface of the central block.

FIG. 2

—PRIOR ART—

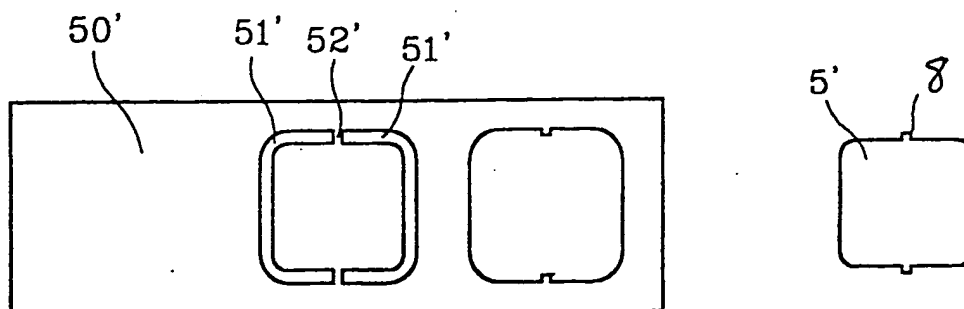


FIG. 6B

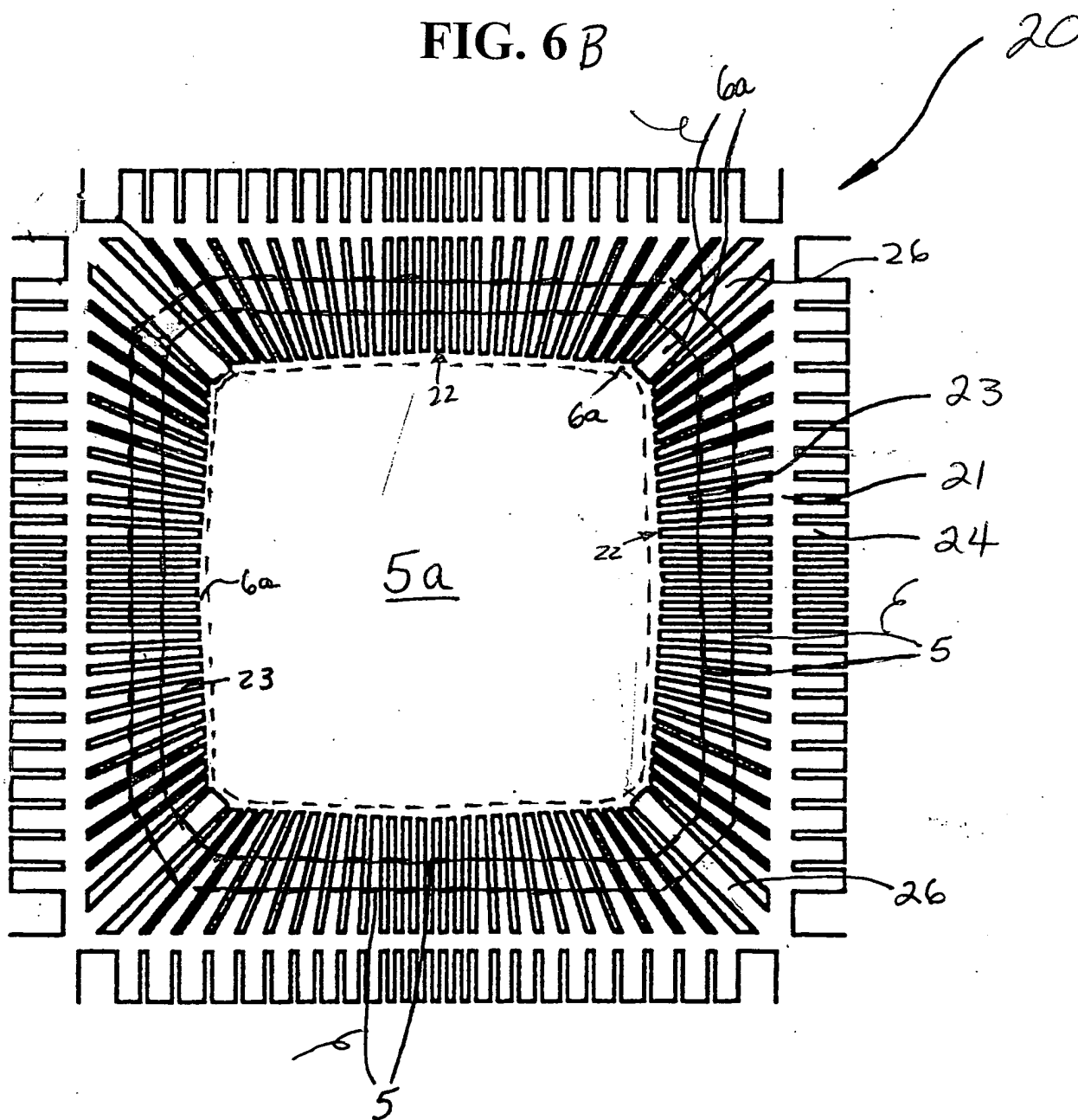


FIG. 8

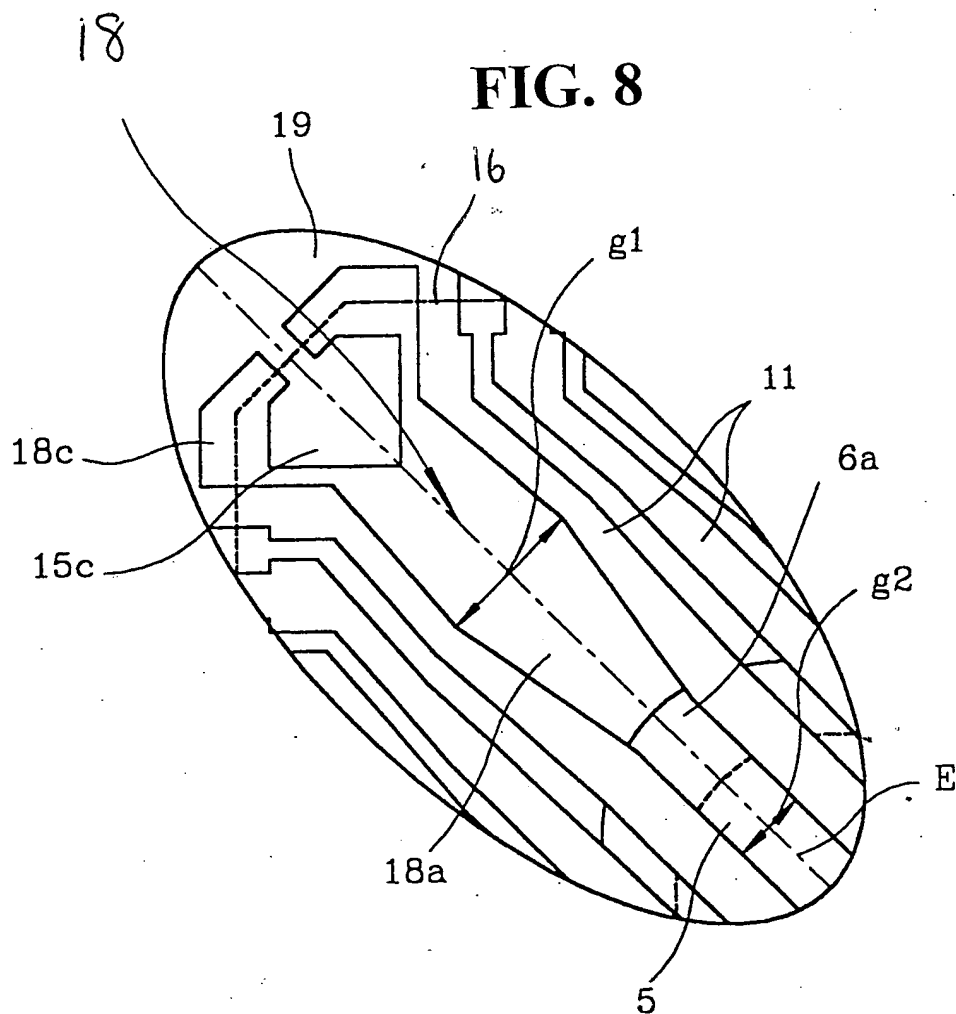


FIG. 9A

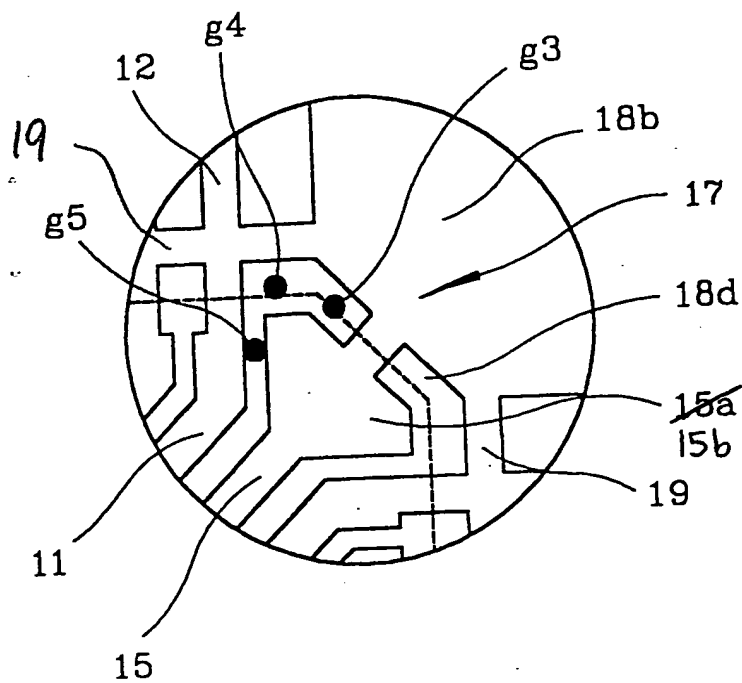


FIG. 9B

